



DSS4240T

40V LOW V_{CE(sat)} NPN SURFACE MOUNT TRANSISTOR

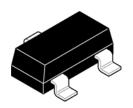
Features

- Ideal for Medium Power Amplification and Switching
- Ultra Low Collector-Emitter Saturation Voltage
- Complimentary NPN Type Available (DSS5240T)
- "Lead-Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

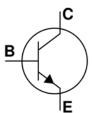
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

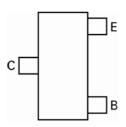
SOT23







Device symbol



Top View Pin Configuration

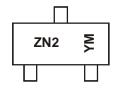
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240T-7	ZN2	7	8	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at https://www.diodes.com/
- 3. Devices with lot number starting from PID0155145 (March 2010) are "Green" products.

Marking Information



ZN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	2010		2011	2012		2013	2014		2015	2016		2017
Code	Χ		Υ	Z		Α	В		С	D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	А
Continuous Collector Current	Ic	2	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_{D}	600	mW
Thermal Resistance, Junction to Ambient Air (Note 4)	$R_{ heta JA}$	209	°C/W
Thermal Resistance, Junction to Lead (Note 5)	$R_{ heta JC}$	74.95	°C/W
Operating and Storage Temperature Range	T_J,T_STG	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	40	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	40	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	V	$I_E = 100 \mu A$
Collector-Base Cutoff Current	1	_	_	100	nA	$V_{CB} = 30V, I_{E} = 0$
Collector-base Cuton Current	ICBO	_	_	50	μΑ	$V_{CB} = 30V, I_{E} = 0, T_{A} = 150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 6)						
		350	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h [300	_	_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h _{FE}	300	_	_] —	$V_{CE} = 2V, I_{C} = 1A$
		150	_	_		$V_{CE} = 2V, I_{C} = 2A$
		_		70		I _C = 100mA, I _B = 1mA
		_	30	100	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_		180		I _C = 750mA, I _B = 15mA
		_		180		$I_C = 1A$, $I_B = 50mA$
		_		320		$I_C = 2A$, $I_B = 200mA$
Equivalent On-Resistance	R _{CE(sat)}	_	60	200	mΩ	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.1	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-on Voltage	V _{BE(on)}	_	_	0.75	V	$V_{CE} = 2V, I_{C} = 100mA$
SMALL SIGNAL CHARACTERISTICS					٠	
Transition Frequency	f⊤	100	_		MHz	$V_{CE} = 10V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	C _{ob}	_	_	20	pF	V _{CB} = 10V, f = 1MHz

Notes:

- 4. Device mounted on FR-4 PCB with minimum recommended pad layout. 5. Thermal resistance from junction to solder-point (at the end of the collector lead). 6. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.



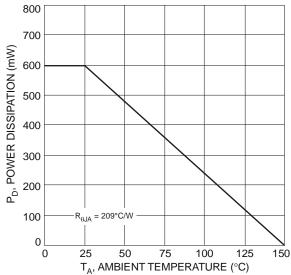


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 4)

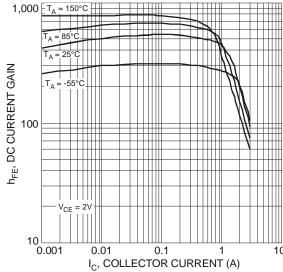
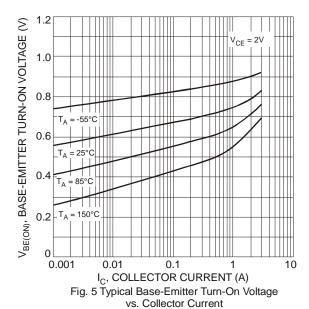
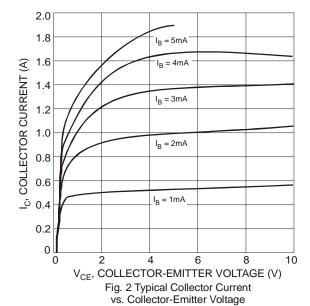


Fig. 3 Typical DC Current Gain vs. Collector Current





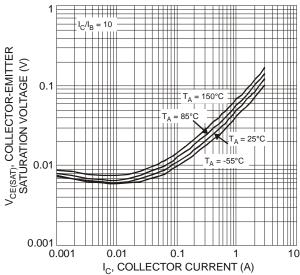


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

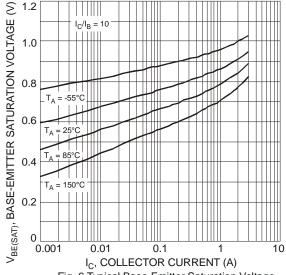
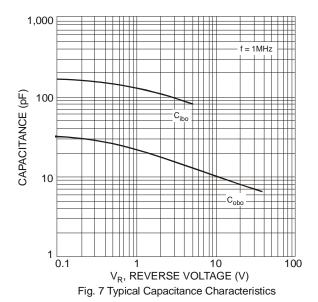
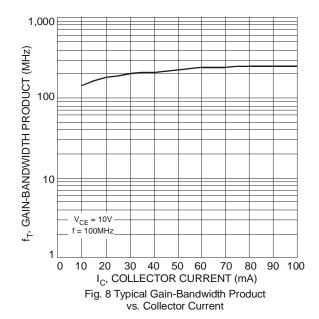


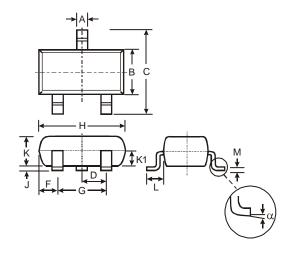
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





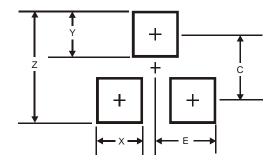


Package Outline Dimensions



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K 1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Y	0.9		
С	2.0		
E	1.35		



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